NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE20ND08U uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =20V,I_D =12A

 $R_{DS(ON)} < 7.1 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$

 $R_{DS(ON)}$ < 7.3m Ω @ V_{GS} =4V

 $R_{DS(ON)} < 7.4 \text{m}\Omega$ @ $V_{GS} = 3.8 \text{V}$

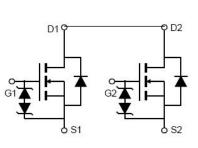
 $R_{DS(ON)}$ < 9.0m Ω @ V_{GS} =3.1V

 $R_{DS(ON)}$ < 10m Ω @ V_{GS} =2.5V

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- 2.5V Drive
- Common-drain type

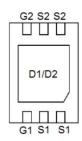
Application

- Battery protection switch
- Mobile device battery charging and discharging



Schematic diagram





Top View

Bottom View

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
20ND08U	NCE20ND08U	DFN2x3 -6L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	Vgs	±12	V
Drain Current-Continuous	I _D	12	Α
Pulsed Drain Current	I _{DM}	48	Α
Maximum Power Dissipation	P _D	1.7	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{ heta JA}$	73.5	°C/W



Electrical Characteristics (TC=25°Cunless otherwise noted)

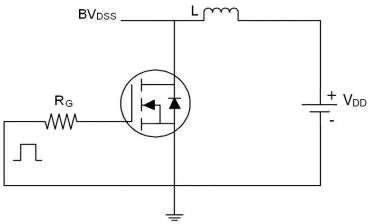
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.5	0.7	1	V
		V _{GS} =4.5V, I _D =5A	-	6.0	7.1	
		V _{GS} =4 V, I _D =5A	-	6.1	7.3	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =3.8V, I _D =5A	-	6.2	7.4	mΩ
		V _{GS} =2.5V, I _D =4A	-	7.5 9 10 1 30 - 1550 - 250 -	9.0	
		V _{GS} =1.8V, I _D =1A	-	10	15	
Forward Transconductance	G FS	V _{DS} =5V,I _D =5A	-	30	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	1/ 40/// 0//	-	1550	-	pF
Output Capacitance	Coss	V_{DS} =10V, V_{GS} =0V, F=1.0MHz	-	250	-	pF
Reverse Transfer Capacitance	C _{rss}	r-1.0IVIDZ	-	210	-	pF
Switching Characteristics (Note 4)	·		•			
Turn-on Delay Time	t _{d(on)}		-	2.0	-	nS
Turn-on Rise Time	t _r	V_{DD} =10 V , I_D =5 A	-	5.5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =4.5 V , R_{GEN} =3 Ω	-	38	-	nS
Turn-Off Fall Time	t _f		-	85	-	nS
Total Gate Charge	Qg	V 40V 04	-	17	-	nC
Gate-Source Charge	Q_{gs}	$V_{DS}=10V,I_{D}=3A,$ $V_{GS}=4.5V$	-	2.0	-	nC
Gate-Drain Charge	Q_{gd}	VGS-4.5V	-	5.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =12A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	12	Α

Notes:

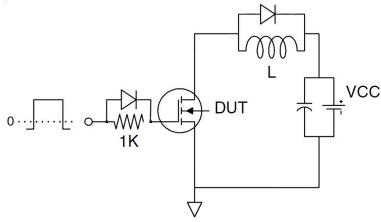
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.
- 4. Guaranteed by design, not subject to production

Test Circuit

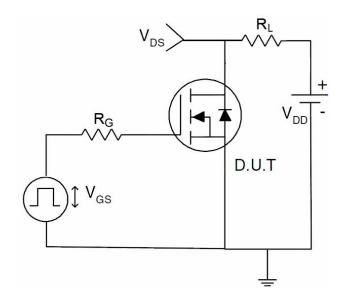
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

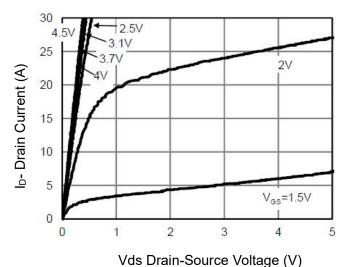


Figure 1 Output Characteristics

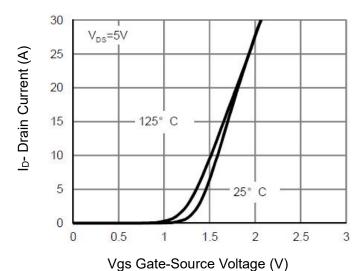


Figure 2 Transfer Characteristics

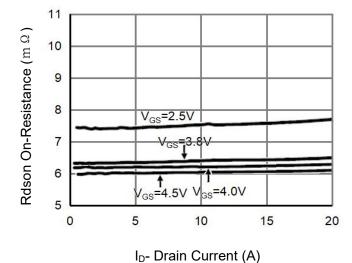


Figure 3 Rdson- Drain Current

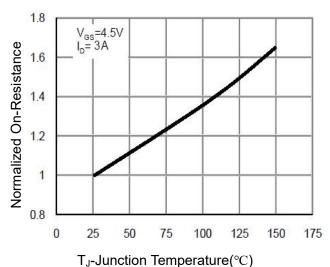


Figure 4 Rdson-Junction Temperature

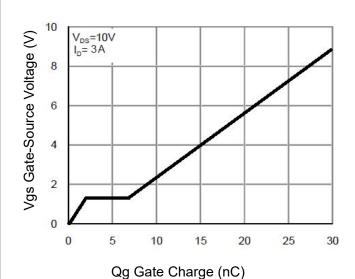


Figure 5 Gate Charge

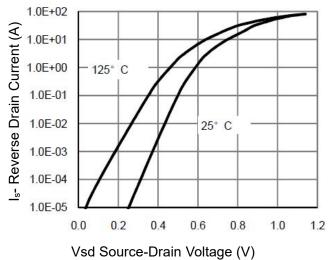


Figure 6 Source- Drain Diode Forward

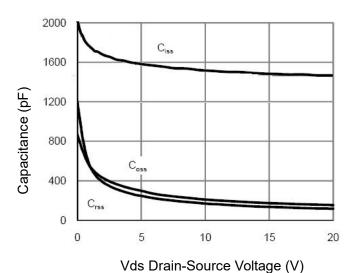


Figure 7 Capacitance vs Vds

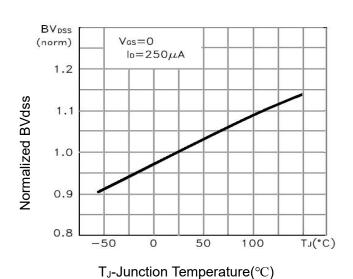


Figure 9 BV_{DSS} vs Junction Temperature

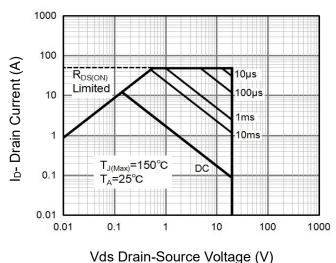


Figure 8 Safe Operation Area

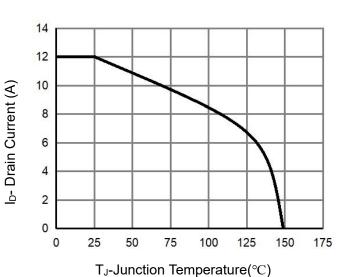


Figure 10 Current De-rating

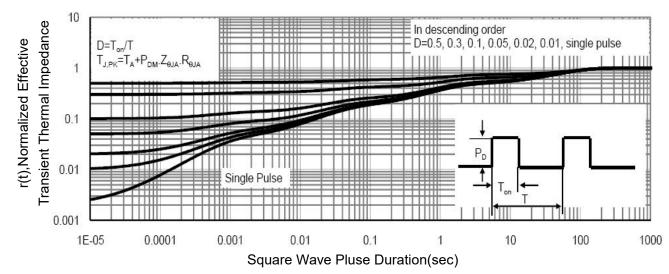
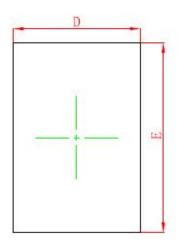
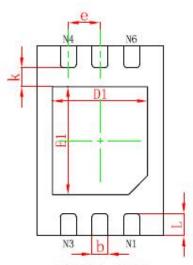


Figure 11 Normalized Maximum Transient Thermal Impedance

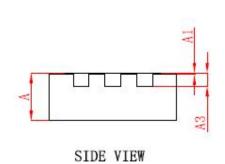
DFN2X3-6L Package Information



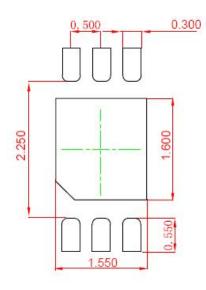
TOP VIEW



VIEW BOTTOM



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A3	0.203REF.		0.008REF.		
D	1.950	2.050	0.077	0.081	
E	2.950	3.050	0.116	0.120	
D1	1.450	1.550	0.057	0.061	
E1	1.650	1.750	0.065	0.069	
k	0.200MIN.		0.008MIN.		
b	0.200	0.300	0.008	0.012	
е	0.500TYP.		0.020TYP.		
L	0.300	0.400	0.012	0.016	



Note:

- 1.Controlling dimension:in millimeters.
- 2,General tolerance;± 0,050mm, 3.The pad layout is for reference purposes only.

NCE20ND08U

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